



STPS20L40CF/CW/CT/CFP

LOW DROP POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_F(AV)$	2 x 10 A
V_{RRM}	40 V
$T_j(max)$	150°C
$V_F(max)$	0.5 V

FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- INSULATED PACKAGE: ISOWATT220AB, TO-220FPAB
Insulating voltage = 200V DC
Capacitance = 12pF
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

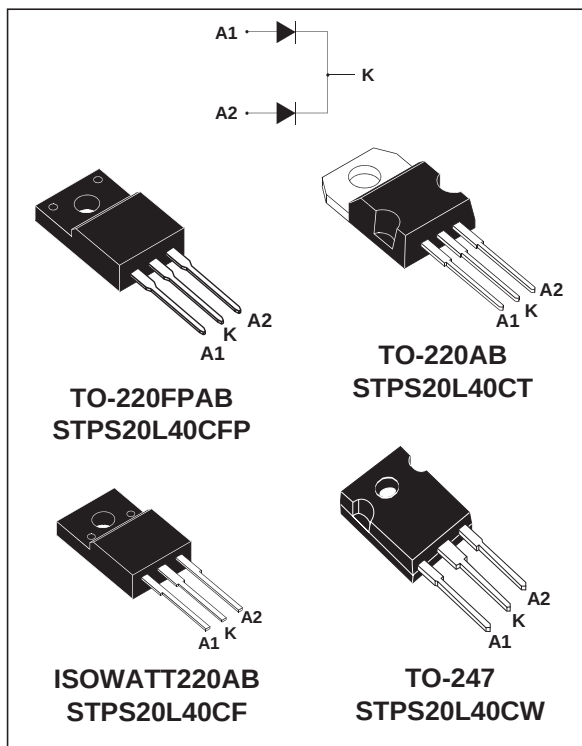
Dual center tap Schottky rectifiers designed for high frequency switched mode power supplies and DC to DC converters.

These devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter				Value	Unit
V _{RRM}	Repetitive peak reverse voltage				40	V
I _{F(RMS)}	RMS forward current				30	A
I _{F(AV)}	Average forward current	TO-220AB	T _c = 135°C	Per diode	10	A
		TO-247	δ = 0.5	Per device	20	
		ISOWATT220AB TO-220FPAB	T _c = 115°C δ = 0.5	Per diode Per device	10 20	A
I _{FSM}	Surge non repetitive forward current		tp = 10 ms Sinusoidal		180	A
I _{RRM}	Peak repetitive reverse current		tp = 2 μs square F=1kHz		1	A
I _{RSM}	Non repetitive peak reverse current		tp = 100 μs square		2	A
P _{ARM}	Repetitive peak avalanche power		tp = 1μs Tj = 25°C		4000	W
T _{stg}	Storage temperature range				- 65 to + 150	°C
Tj	Maximum operating junction temperature *				150	°C
dV/dt	Critical rate of rise of reverse voltage				10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j - a)}$ thermal runaway condition for a diode on its own heatsink



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THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	ISOWATT220AB TO-220FPAB	Per diode	4.5	$^{\circ}\text{C/W}$
			Total	3.5	
			Coupling	2.5	
$R_{th(j-c)}$	Junction to case	TO-247	Per diode	2.2	$^{\circ}\text{C/W}$
			Total	1.20	
			Coupling	0.3	
$R_{th(j-c)}$	Junction to case	TO-220AB	Per diode	2.2	$^{\circ}\text{C/W}$
			Total	1.3	
			Coupling	0.3	

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			0.7	mA
		$T_j = 100^{\circ}\text{C}$			15	35	mA
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 10\text{ A}$			0.55	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 10\text{ A}$		0.44	0.5	
		$T_j = 25^{\circ}\text{C}$	$I_F = 20\text{ A}$			0.73	
		$T_j = 125^{\circ}\text{C}$	$I_F = 20\text{ A}$		0.62	0.72	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.28 \times I_{F(AV)} + 0.022 I_F^2(\text{RMS})$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

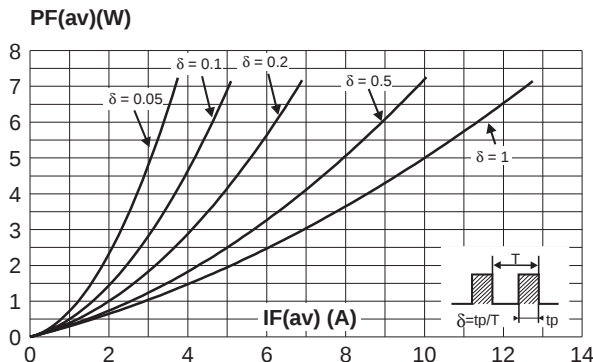


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).

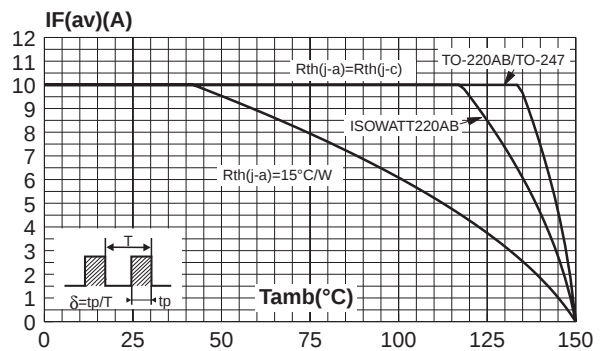


Fig. 3: Normalized avalanche power derating versus pulse duration.

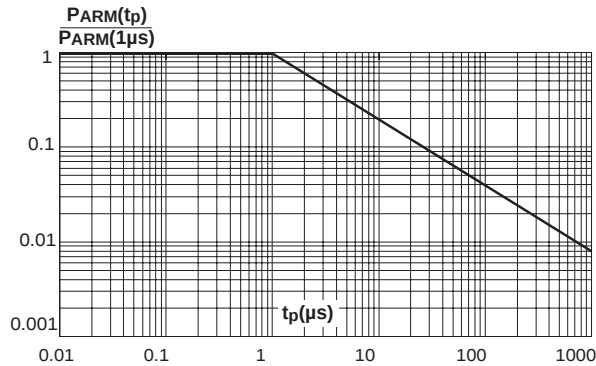


Fig. 4: Normalized avalanche power derating versus junction temperature.

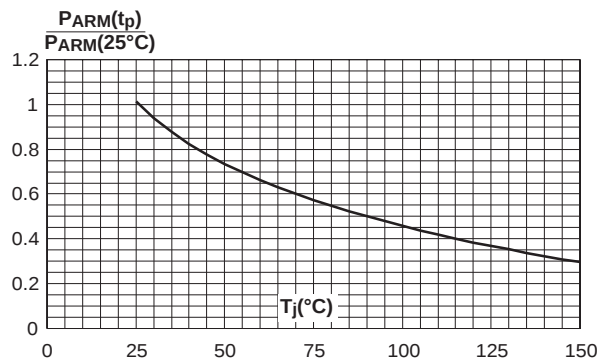


Fig. 5-1: Non repetitive surge peak forward current versus overload duration (maximum values, per diode, TO-220AB / TO-247).

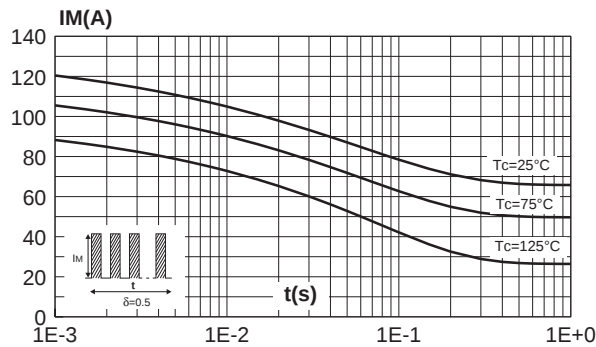


Fig. 5-2: Non repetitive surge peak forward current versus overload duration (maximum values, per diode, ISOWATT220AB, TO-220FPAB).

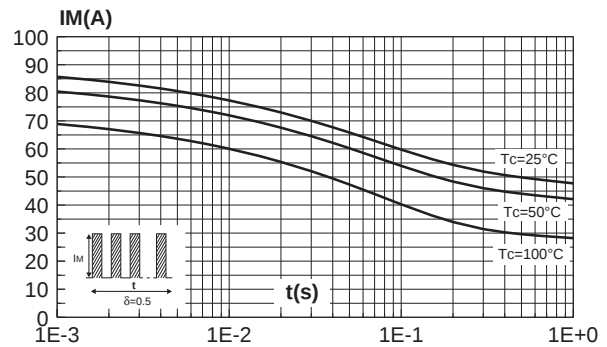


Fig. 6-1: Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB / TO-247).

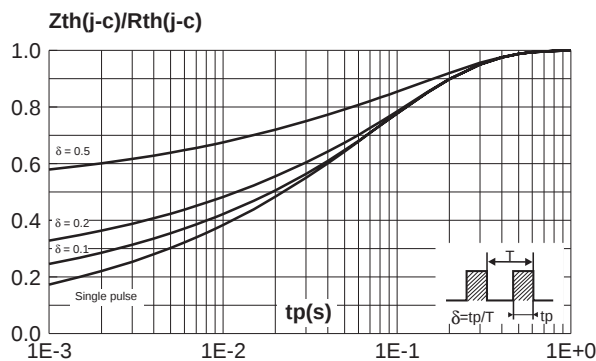


Fig. 6-2: Relative variation of thermal impedance junction to case versus pulse duration (ISOWATT220AB, TO-220FPAB).

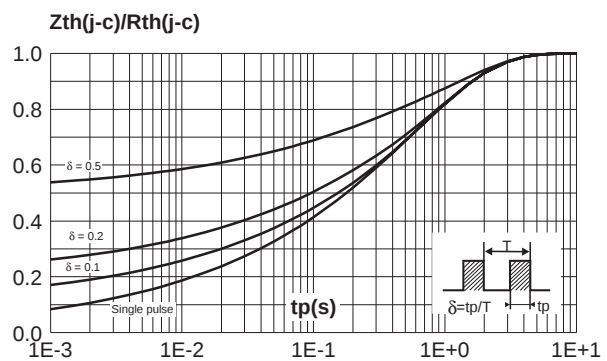


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

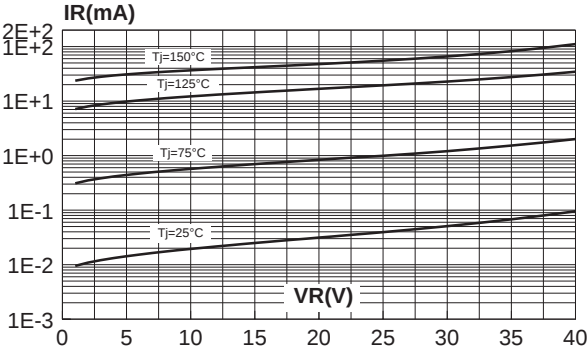


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

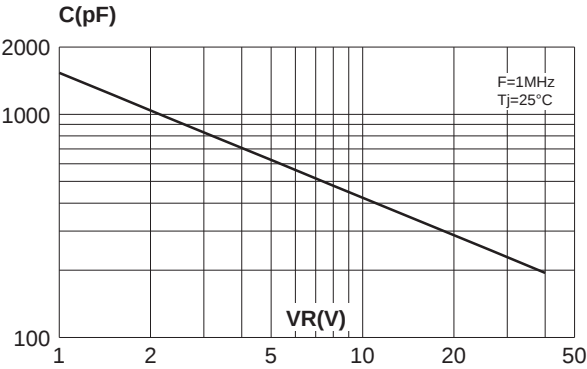
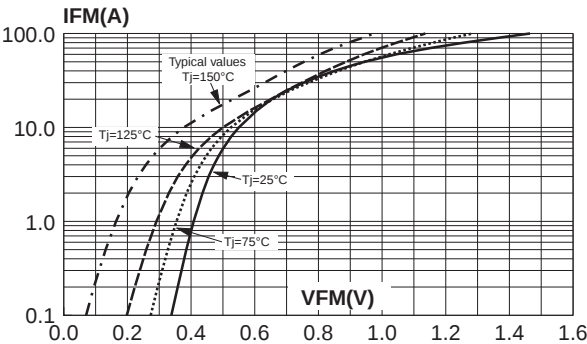
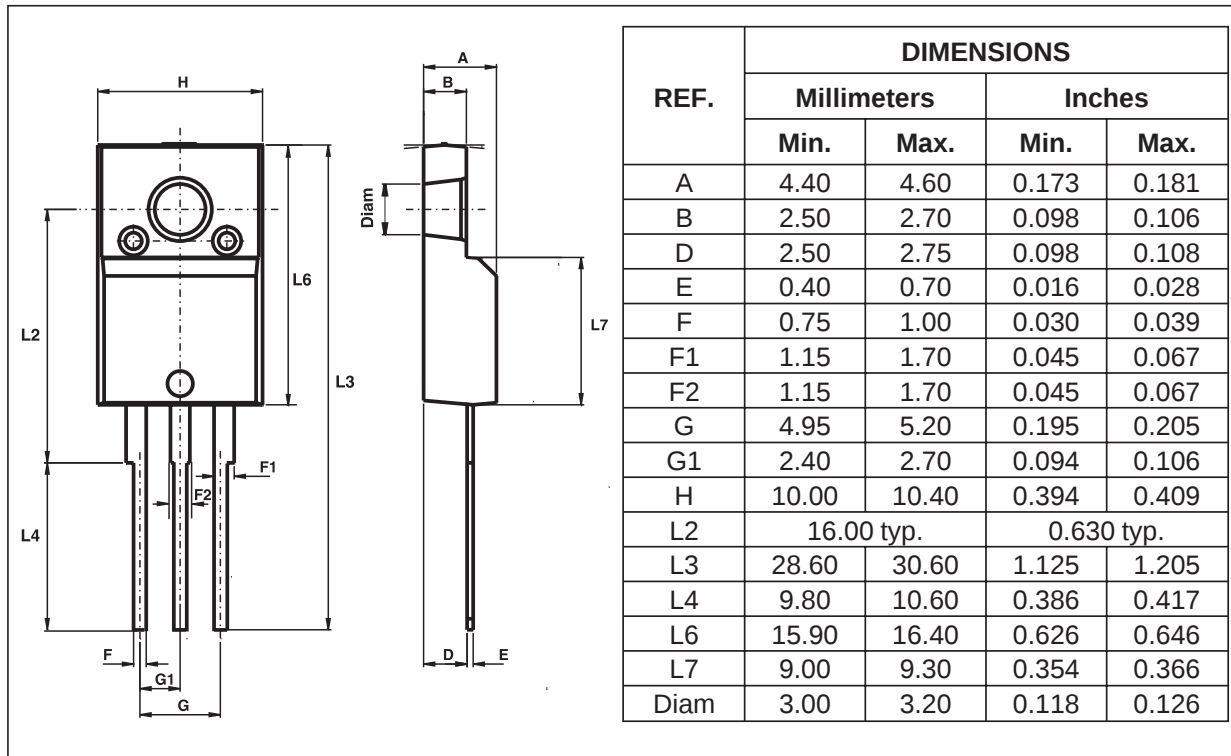


Fig. 9: Forward voltage drop versus forward current (maximum values) (per diode).

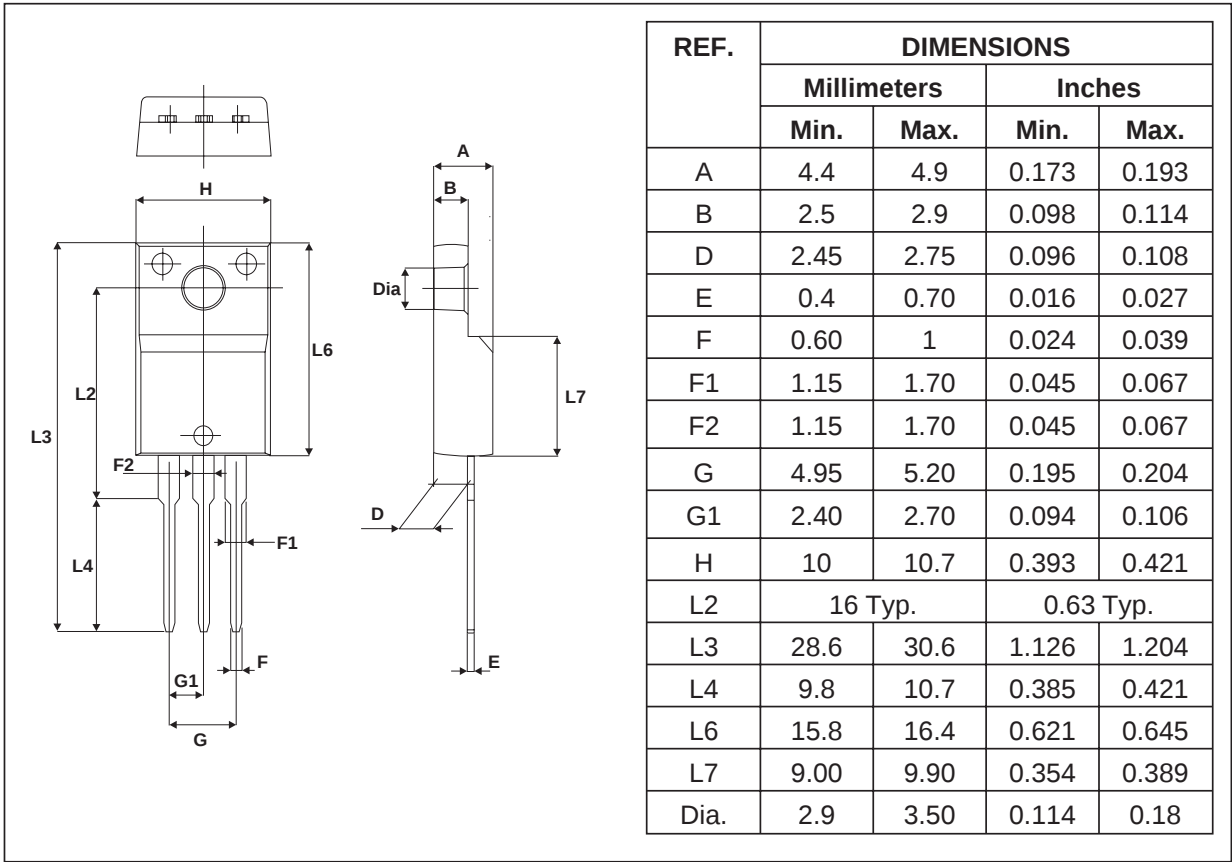


PACKAGE MECHANICAL DATA
ISOWATT220AB

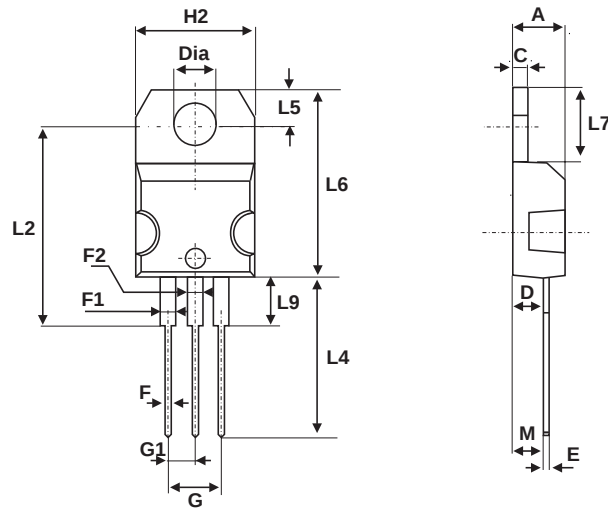


- Cooling method : C
- Recommended torque value : 0.55 m.N
- Maximum torque value : 0.70 m.N

PACKAGE MECHANICAL DATA
TO-220FPAB



- Cooling method : C
- Recommended torque value : 0.55 m.N
- Maximum torque value : 0.70 m.N

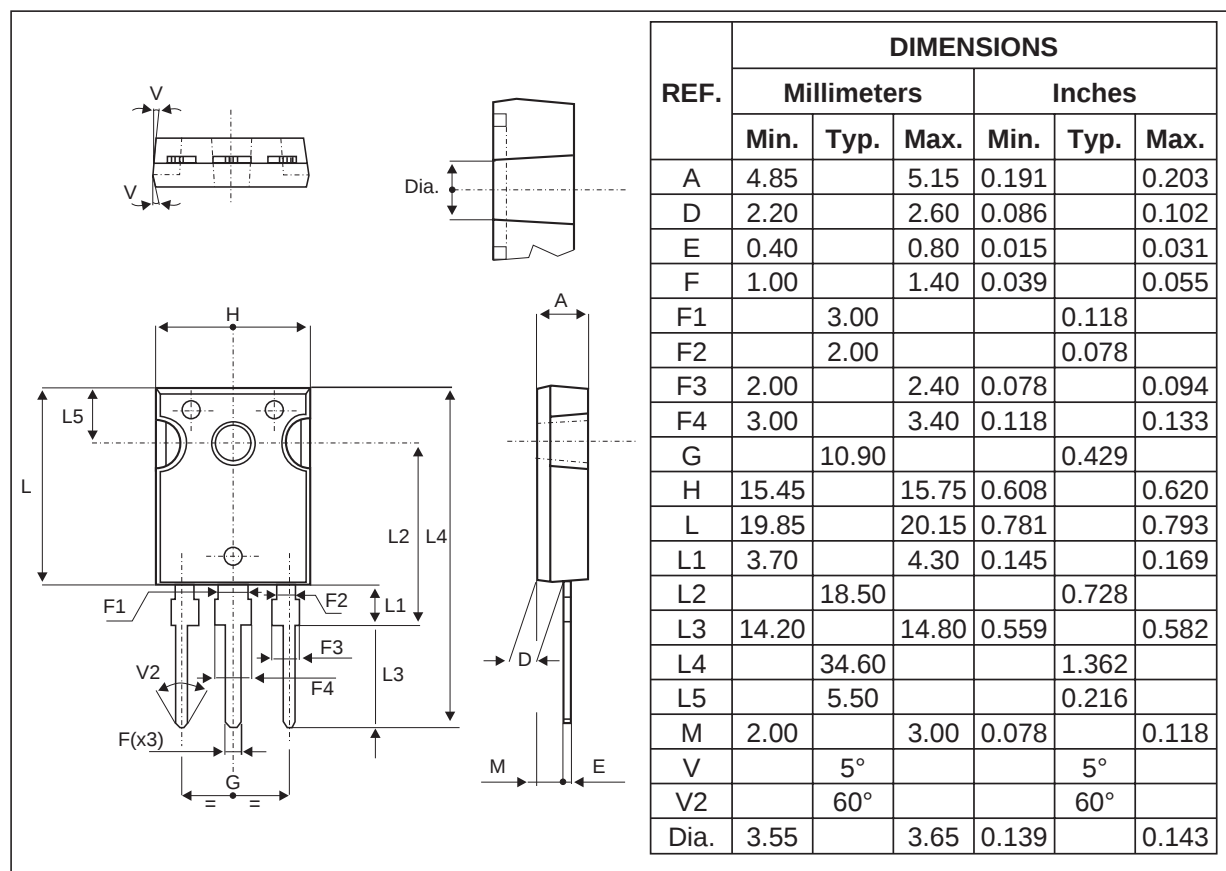
PACKAGE MECHANICAL DATA
 TO-220AB


REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

- Cooling method : C
- Recommended torque value : 0.55 m.N
- Maximum torque value : 0.70 m.N

STPS20L40CF/CW/CT/CFP**PACKAGE MECHANICAL DATA**

TO-247



- Cooling method : C
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20L40CF	STPS20L40CF	ISOWATT220AB	2.1g	50	Tube
STPS20L40CFP	STPS20L40CFP	TO-220FPAB	2g	50	Tube
STPS20L40CT	STPS20L40CT	TO-220AB	2g	50	Tube
STPS20L40CW	STPS20L40CW	TO-247	4.4g	30	Tube

- Epoxy meets UL94,V0

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